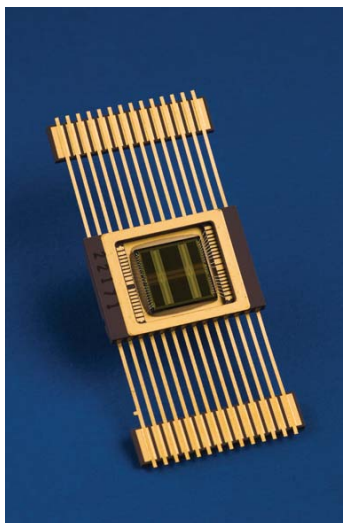
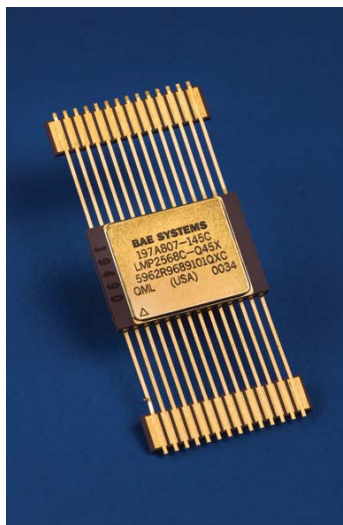


Programmable read-only memory 32K x 8 radiation-hardened PROM – low power 3.3V

FEATURES AND CAPABILITIES

The PROM is fabricated with BAE Systems' QML-qualified radiation-hardened technology and is designed for use in systems operating in radiation environments. The radiation-hardened oxide-nitride-oxide anti-fuse technology features, 3.3 V transistors in the data path, and high-voltage N and PFETs in the programming path circuitry. The PROM operates over the full military temperature range, requires a single 3.3 V \pm 5% power supply, and is available with TTL-compatible I/O. Power consumption is typically 15 mW/MHz in operation and is less than 10 mW/MHz in the low-power-enabled mode. The PROM operation is fully asynchronous, with an associated typical access time of less than 60 nanoseconds. Synchronous operation is also possible using CE as a clock.



- Read/write cycle times \leq 100 ns
- Operation from -55°C to 125°C
- SMD number: 5962G02502
- BAE Systems part number: 238A790
- Asynchronous operation
- TTL-compatible I/O
- Single 3.3V \pm 5% power supply
- Low operating power
- 28-lead flat pack (0.500" x 0.720")
- Radiation levels
 - Fabricated with BAE Systems bulk CMOS technology
 - Total-dose hardness through 2×10^5 rad(Si)
 - Neutron-hardness through 1×10^{12} N/cm²
 - SEU immune (no latches)
 - Latchup-free

SIGNAL DEFINITIONS

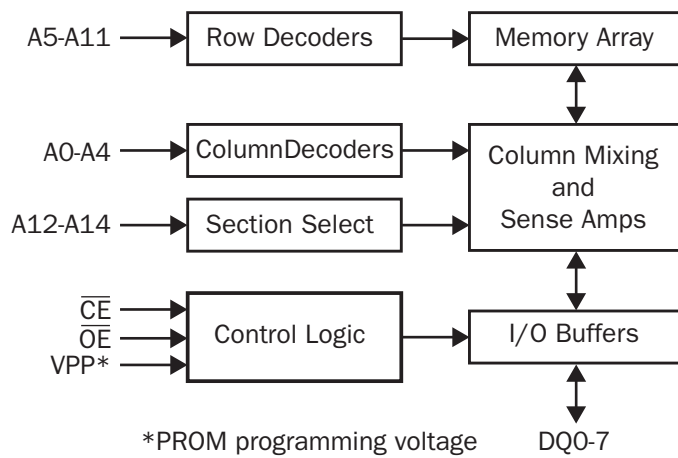
A:0-14 Address input pins that select a particular eight-bit word within the memory array.

DQ:0-7 Bi-directional data pins that serve as data outputs during a read operation and as data inputs during a write operation.

\overline{OE} Negative output enable, when at a high level, holds the data output drivers in a high impedance state. In programming mode, with \overline{OE} high and \overline{CE} low, data driver state is in "Data-In" to enable programming.

\overline{CE} Chip enable, when at a low level with \overline{OE} at low level, allows normal operation. When at a high level, \overline{CE} forces the data output drivers in a high impedance state.

FUNCTIONAL DIAGRAM



FOR MORE INFORMATION, CONTACT:

BAE Systems
9300 Wellington Road
Manassas, VA 20110-4122
Tel: 1-866-530-8104
www.baesystems.com/sse